

# Thyristor Module

$V_{RRM} = 2 \times 1200 \text{ V}$

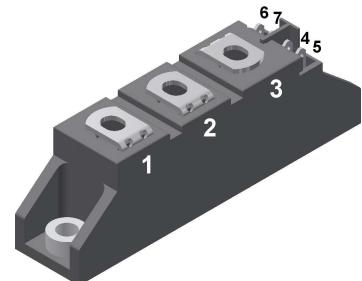
$I_{TAV} = 85 \text{ A}$

$V_T = 1.34 \text{ V}$

## Phase leg

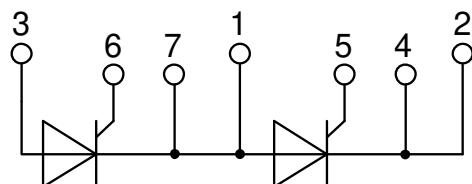
### Part number

**MCC72-12io1B**



Backside: isolated

 E72873



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

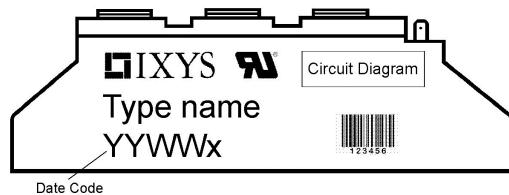
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**Thyristor**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200 V$ $V_{R/D} = 1200 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		200 5	$\mu A$ mA
$V_T$	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^\circ C$		1.34	V
		$I_T = 300 A$			1.74	V
		$I_T = 150 A$	$T_{VJ} = 125^\circ C$		1.34	V
		$I_T = 300 A$			1.82	V
$I_{TAV}$	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 125^\circ C$		85	A
$I_{T(RMS)}$	RMS forward current	180° sine			133	A
$V_{T0}$	threshold voltage	$r_T$ slope resistance } for power loss calculation only	$T_{VJ} = 125^\circ C$		0.85	V
	slope resistance				3.2	$m\Omega$
$R_{thJC}$	thermal resistance junction to case				0.3	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.2		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ C$		333	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		1.70	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		1.84	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		1.45	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		1.56	kA
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		14.5	$kA^2s$
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		14.0	$kA^2s$
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		10.4	$kA^2s$
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		10.1	$kA^2s$
$C_J$	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	119		pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^\circ C$		10	W
		$t_p = 300 \mu s$			5	W
					0.5	W
$P_{GAV}$	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 250 A$			150	$A/\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$				
		$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 85 A$			500	$A/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		1000	$V/\mu s$
		$R_{GK} = \infty$ ; method 1 (linear voltage rise)				
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		2.5	V
			$T_{VJ} = -40^\circ C$		2.6	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		150	mA
			$T_{VJ} = -40^\circ C$		200	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		0.2	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		450	mA
$I_H$	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ C$		2	$\mu s$
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 150 A; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 100^\circ C$ $di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$		185		$\mu s$

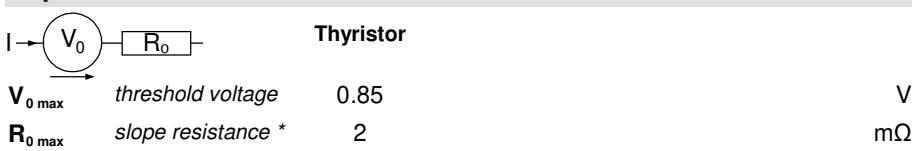
Package TO-240AA			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			200	A
$T_{VJ}$	virtual junction temperature		-40		125	°C
$T_{op}$	operation temperature		-40		100	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				81		g
$M_D$	mounting torque		2.5		4	Nm
$M_T$	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air		terminal to terminal	13.0	9.7	mm
$d_{Spb/Apb}$			terminal to backside	16.0	16.0	mm
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		4800		V
				4000		V



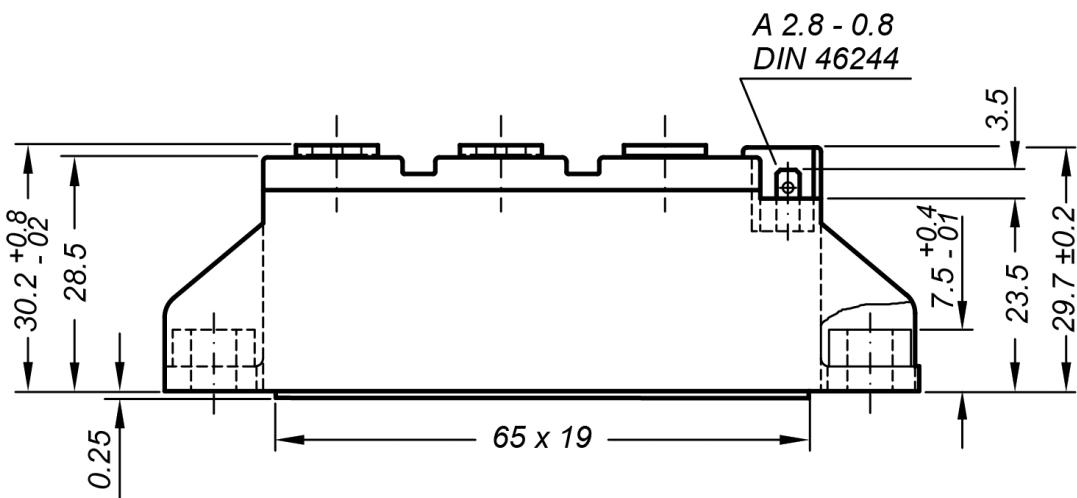
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC72-12io1B	MCC72-12io1B	Box	36	458198

Similar Part	Package	Voltage class
MCMA85P1200TA	TO-240AA-1B	1200
MCMA110P1200TA	TO-240AA-1B	1200

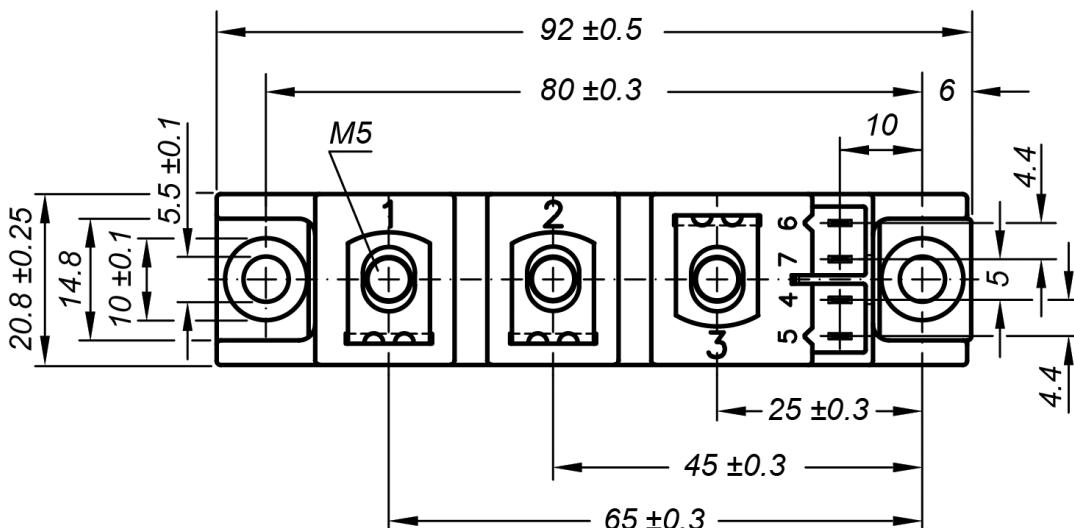
### Equivalent Circuits for Simulation

\* on die level
 $T_{VJ} = 125^\circ\text{C}$ 


## **Outlines TO-240AA**

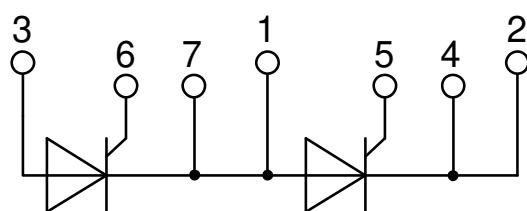


*General tolerance: DIN ISO 2768 class „c“*



#### Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 200L (L = Left for pin pair 4/5)      } UL 758, style 3751  
Type ZY 200R (R = Right for pin pair 6/7)      }



## Thyristor

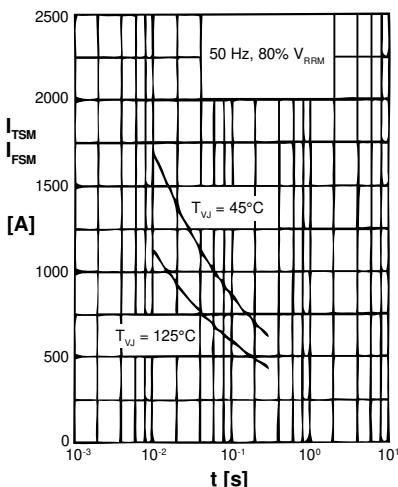


Fig. 1 Surge overload current  
 $I_{TSM}, I_{FSM}$ : Crest value,  $t$ : duration

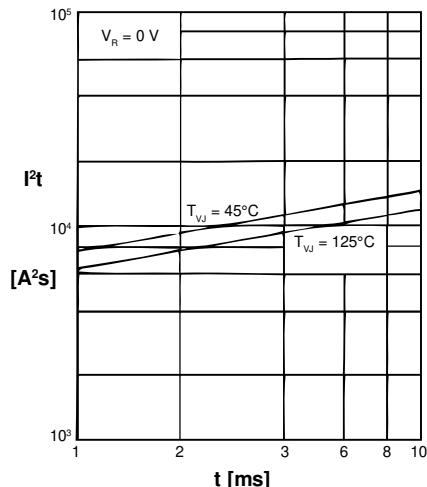


Fig. 2  $I^2t$  versus time (1-10 ms)

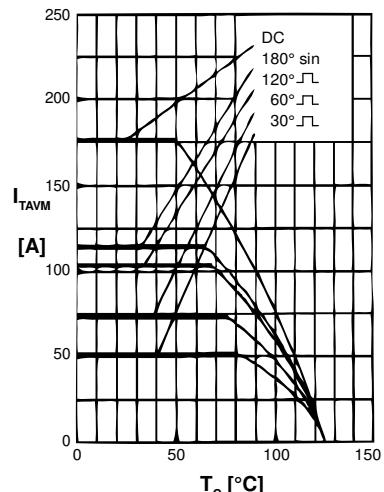


Fig. 3 Maximum forward current at case temperature

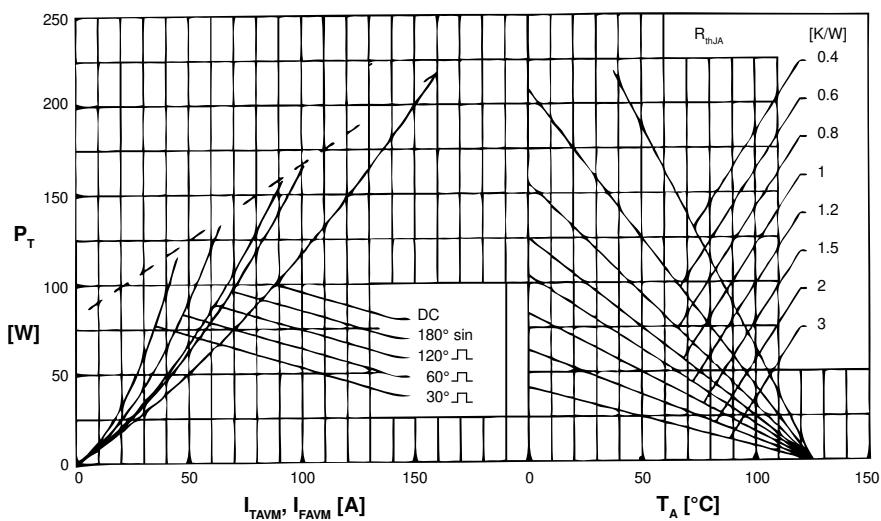


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per thyristor/diode)

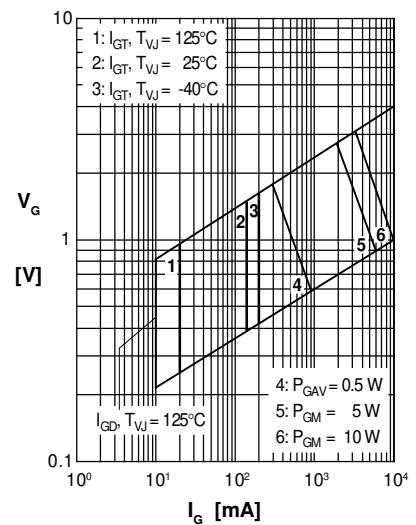


Fig. 5 Gate trigger characteristics

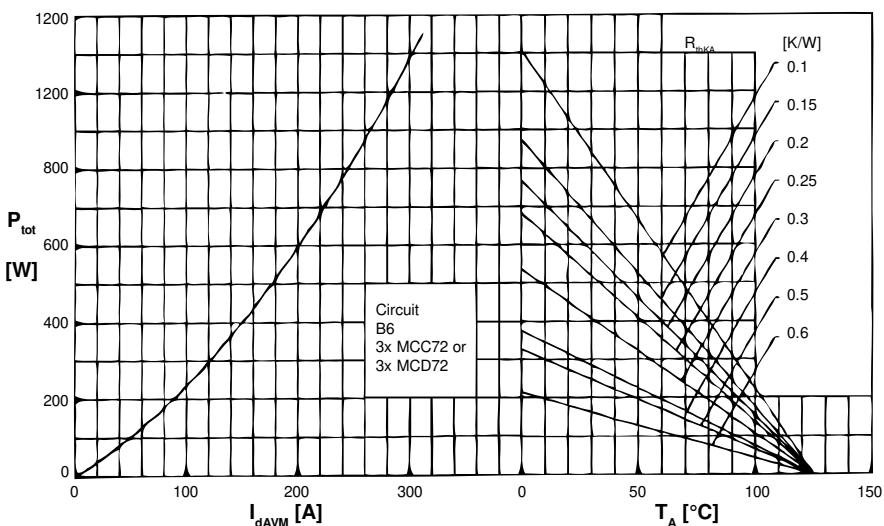


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

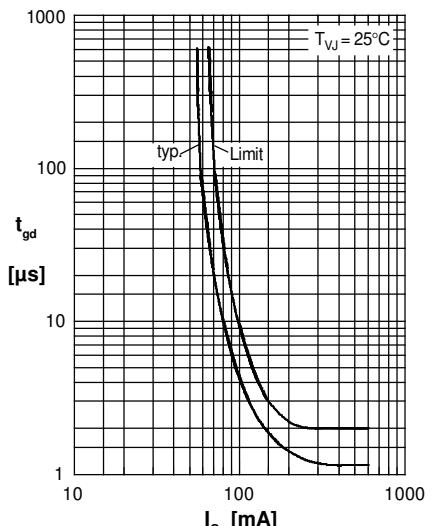


Fig. 7 Gate trigger delay time

## Thyristor

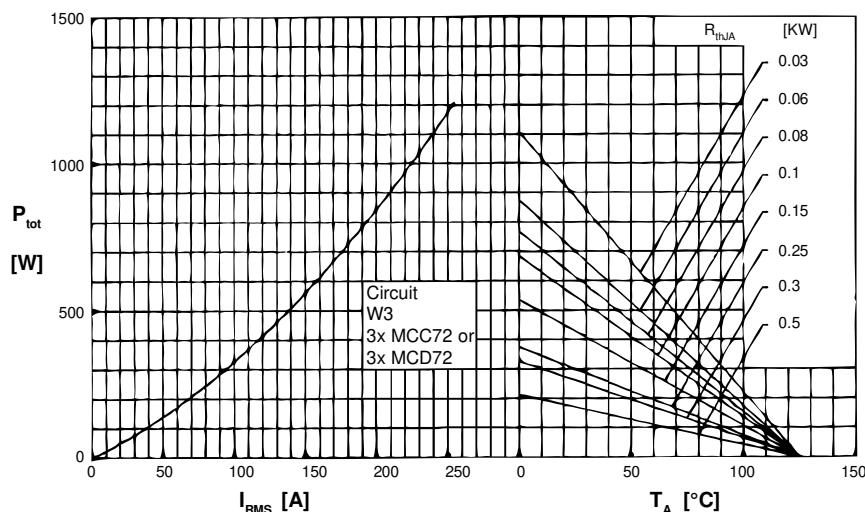


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

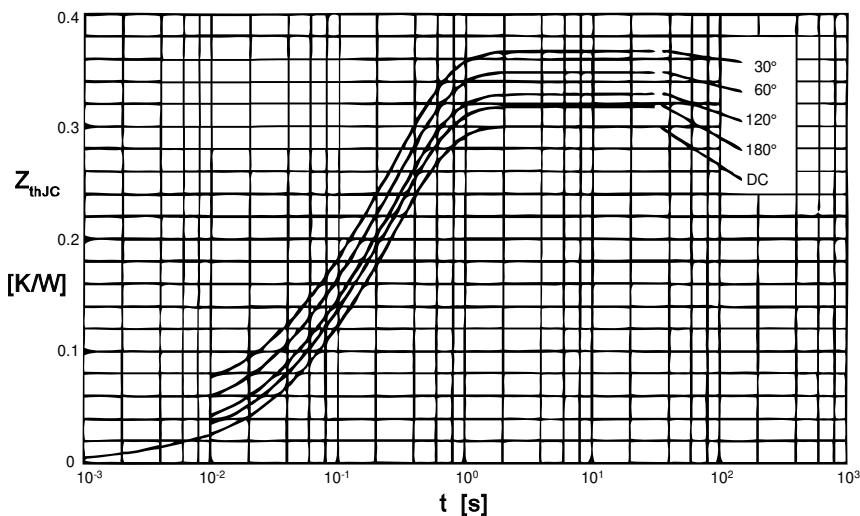


Fig. 9 Transient thermal impedance junction to case (per thyristor)

$R_{thJC}$  for various conduction angles  $d$ :

$d$	$R_{thJC}$ [K/W]
DC	0.30
180°	0.31
120°	0.33
60°	0.35
30°	0.37

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.008	0.0019
2	0.054	0.0470
3	0.238	0.3000

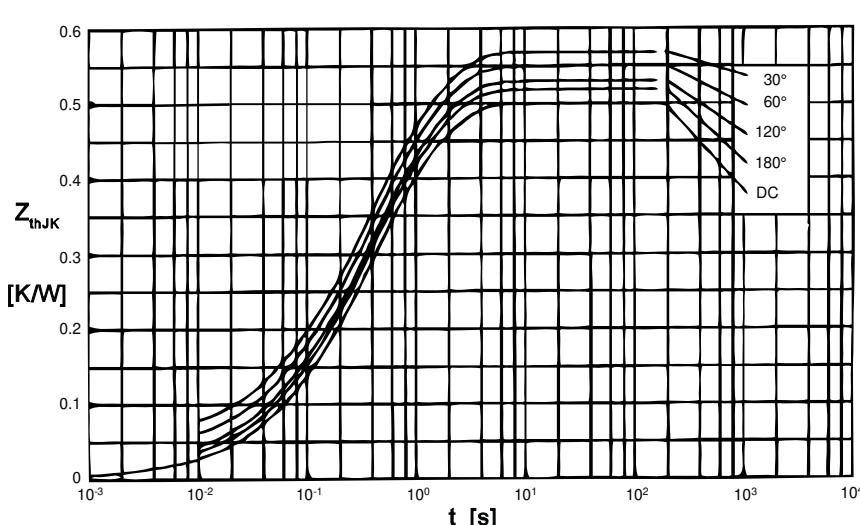


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

$R_{thJK}$  for various conduction angles  $d$ :

$d$	$R_{thJK}$ [K/W]
DC	0.50
180°	0.51
120°	0.53
60°	0.55
30°	0.57

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.008	0.0019
2	0.054	0.0470
3	0.238	0.3000
4	0.200	1.2500



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Электрон  
Связь**

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